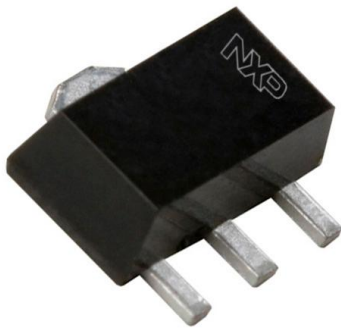


# PBHV8550XF Datasheet

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DiGi Electronics Part Number	PBHV8550XF-DG
Manufacturer	<a href="#">Nexperia USA Inc.</a>
Manufacturer Product Number	PBHV8550XF
Description	TRANS NPN 500V 0.15A SOT89
Detailed Description	Bipolar (BJT) Transistor NPN 500 V 150 mA 35MHz 5 20 mW Surface Mount SOT-89



Tel: +00 852-30501935

RFQ Email: [Info@DiGi-Electronics.com](mailto:Info@DiGi-Electronics.com)

DiGi is a global authorized distributor of electronic components.

## Purchase and inquiry

**Manufacturer Product Number:**

PBHV8550XF

**Series:**

-

**Transistor Type:**

NPN

**Voltage - Collector Emitter Breakdown (Max):**

500 V

**Current - Collector Cutoff (Max):**

100nA

**Power - Max:**

520 mW

**Operating Temperature:**

150°C (TJ)

**Qualification:**

AEC-Q101

**Package / Case:**

TO-243AA

**Base Product Number:**

PBHV8550

**Manufacturer:**

Nexperia USA Inc.

**Product Status:**

Active

**Current - Collector (Ic) (Max):**

150 mA

**Vce Saturation (Max) @ Ib, Ic:**

90mV @ 6mA, 50mA

**DC Current Gain (hFE) (Min) @ Ic, Vce:**

50 @ 50mA, 10V

**Frequency - Transition:**

35MHz

**Grade:**

Automotive

**Mounting Type:**

Surface Mount

**Supplier Device Package:**

SOT-89

## Environmental & Export classification

**RoHS Status:**

ROHS3 Compliant

**REACH Status:**

REACH Unaffected

**HTSUS:**

8541.21.0095

**Moisture Sensitivity Level (MSL):**

1 (Unlimited)

**ECCN:**

EAR99



# PBHV8550X

500 V, 150 mA NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

9 October 2024

Product data sheet

## 1. General description

NPN high-voltage low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a medium power SOT89 (SC-62) flat lead Surface-Mounted Device (SMD) plastic package.

## 2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- AEC-Q101 qualified

## 3. Applications

- Electronic ballasts
- LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- Flyback converters
- Switch Mode Power Supply (SMPS)

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	500	V
I <sub>C</sub>	collector current		-	-	150	mA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 30 mA; T <sub>amb</sub> = 25 °C	50	100	-	

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	<p>SOT89</p>	<p>sym123</p>
2	C	collector		
3	B	base		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBHV8550X	SOT89	plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	<a href="#">SOT89</a>

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PBHV8550X	C8

## 8. Limiting values

Table 5. Limiting values

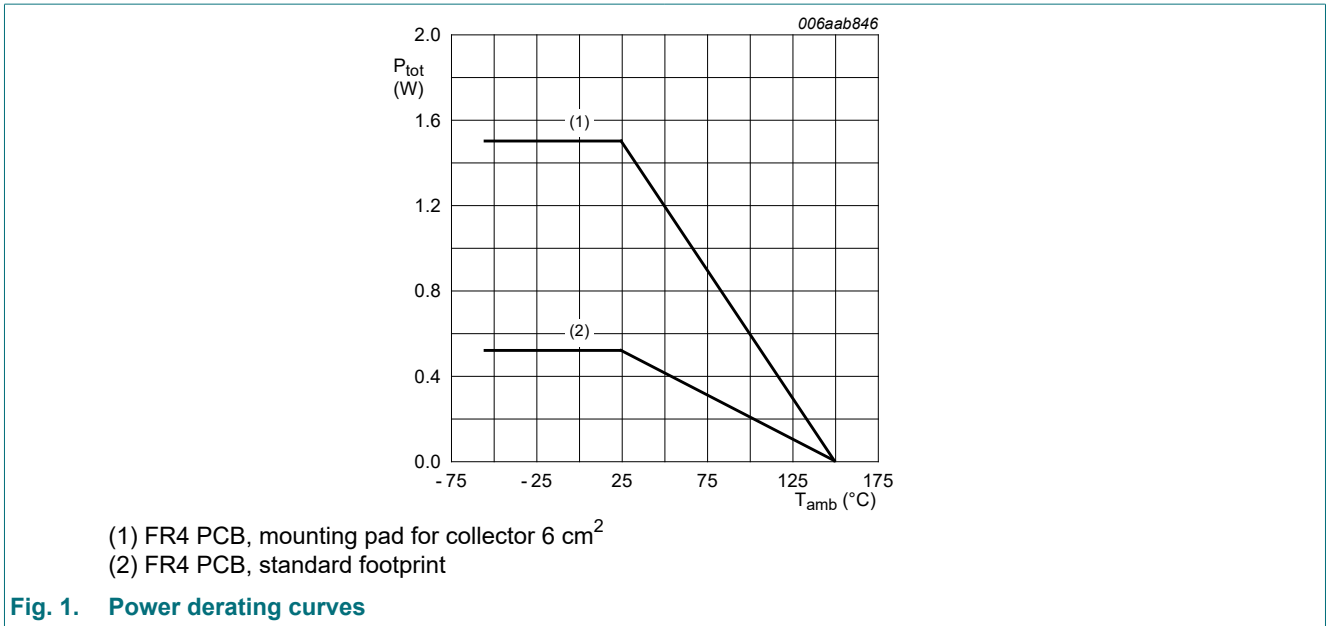
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	500	V
$V_{CEO}$	collector-emitter voltage	open base		-	500	V
$V_{CESM}$	collector-emitter peak voltage	$V_{BE} = 0$ V		-	500	V
$V_{EBO}$	emitter-base voltage	open collector		-	6	V
$I_C$	collector current			-	150	mA
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1$ ms		-	0.5	A
$I_{BM}$	peak base current			-	200	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	520	mW
			[2]	-	1.5	W
$T_j$	junction temperature			-	150	°C
$T_{amb}$	ambient temperature			-55	150	°C
$T_{stg}$	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 6 cm<sup>2</sup>.

500 V, 150 mA NPN high-voltage low VCEsat (BISS) transistor

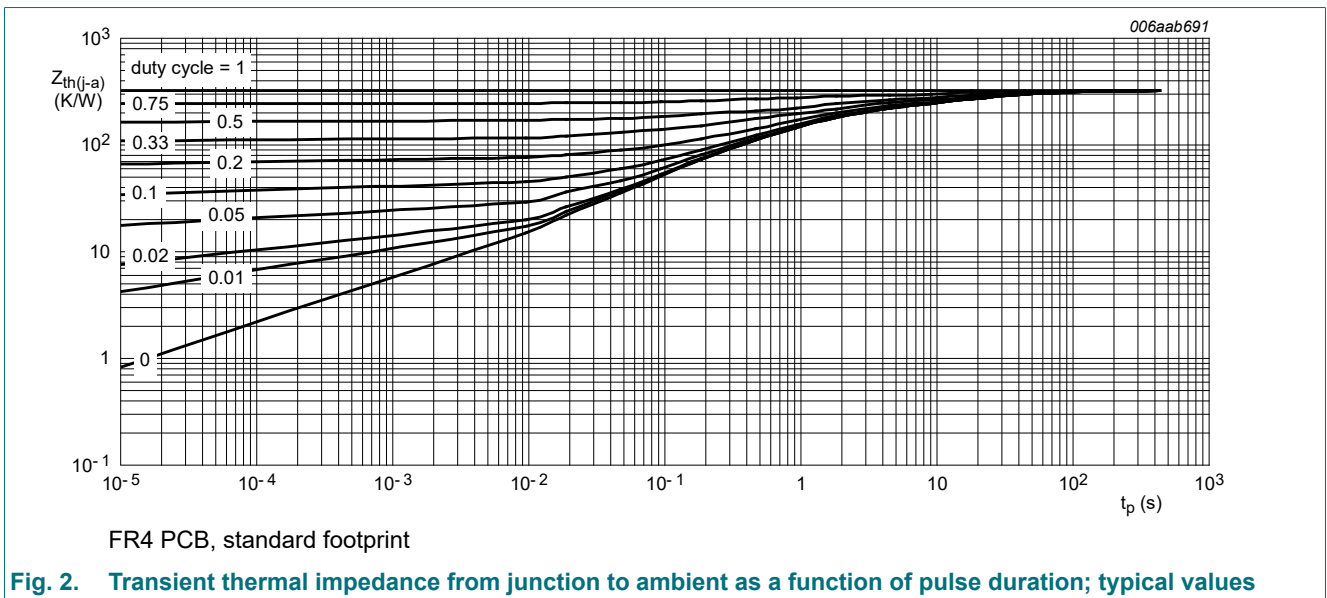


9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	241	K/W
			[2]	-	-	84	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 6 cm<sup>2</sup>.

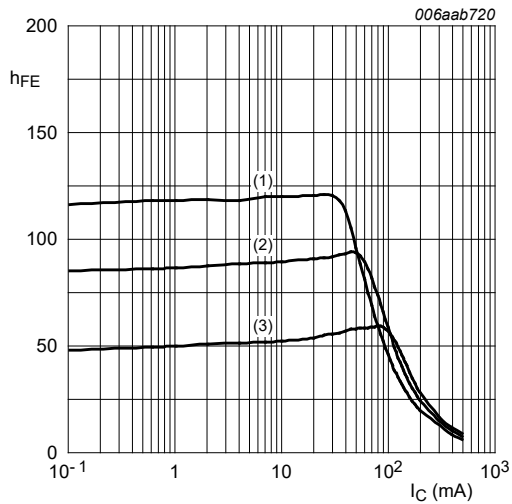


## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 100 \mu\text{A}; I_E = 0 \text{ A}; T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	500	-	-	V
$V_{(BR)CES}$	collector-emitter breakdown voltage (base shorted)	$I_C = 2.5 \text{ mA}; V_{BE} = 0 \text{ V}; T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	500	-	-	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_E = 100 \mu\text{A}; I_C = 0 \text{ A}; T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	6	-	-	V
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 360 \text{ V}; I_E = 0 \text{ A}; T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	-	-	100	nA
		$V_{CB} = 360 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ }^\circ\text{C}$	-	-	50	$\mu\text{A}$
$I_{CES}$	collector-emitter cut-off current	$V_{CE} = 360 \text{ V}; V_{BE} = 0 \text{ V}; T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	-	-	100	nA
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}; T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	-	-	100	nA
$h_{FE}$	DC current gain	$V_{CE} = 10 \text{ V}; I_C = 30 \text{ mA}; T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	50	100	-	
		$V_{CE} = 10 \text{ V}; I_C = 50 \text{ mA}; \text{pulsed}; t_p \leq 300 \mu\text{s}; \delta \leq 0.02; T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	50	100	-	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 20 \text{ mA}; I_B = 2 \text{ mA}; T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	-	60	75	mV
		$I_C = 50 \text{ mA}; I_B = 6 \text{ mA}; \text{pulsed}; t_p \leq 300 \mu\text{s}; \delta \leq 0.02; T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	-	65	90	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}; \text{pulsed}; t_p \leq 300 \mu\text{s}; \delta \leq 0.02; T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	-	0.75	0.9	V
$t_d$	delay time	$V_{CC} = 20 \text{ V}; I_C = 0.05 \text{ A}; I_{B\text{on}} = 5 \text{ mA}; I_{B\text{off}} = -5 \text{ mA}; T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	-	80	-	ns
$t_r$	rise time		-	2700	-	ns
$t_{\text{on}}$	turn-on time		-	2780	-	ns
$t_s$	storage time		-	3400	-	ns
$t_f$	fall time		-	800	-	ns
$t_{\text{off}}$	turn-off time		-	4200	-	ns
$f_T$	transition frequency		$V_{CE} = 10 \text{ V}; I_C = 10 \text{ mA}; f = 100 \text{ MHz}; T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	-	35	-
$C_c$	collector capacitance	$V_{CB} = 20 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	-	4	-	pF
$C_e$	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = 0 \text{ A}; i_c = 0 \text{ A}; f = 1 \text{ MHz}; T_{\text{amb}} = 25 \text{ }^\circ\text{C}$	-	200	-	pF

## 500 V, 150 mA NPN high-voltage low VCEsat (BISS) transistor



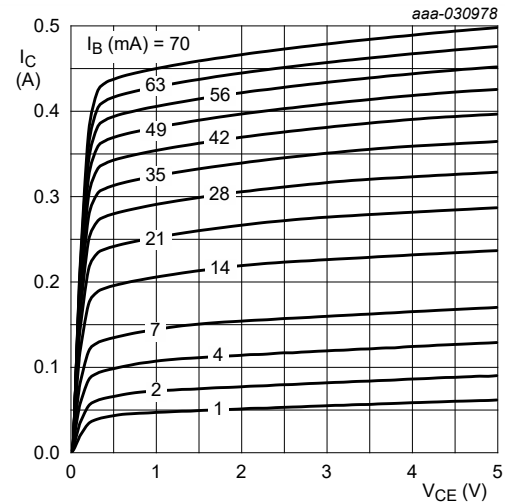
$V_{CE} = 10 \text{ V}$

(1)  $T_{amb} = 100 \text{ }^\circ\text{C}$

(2)  $T_{amb} = 25 \text{ }^\circ\text{C}$

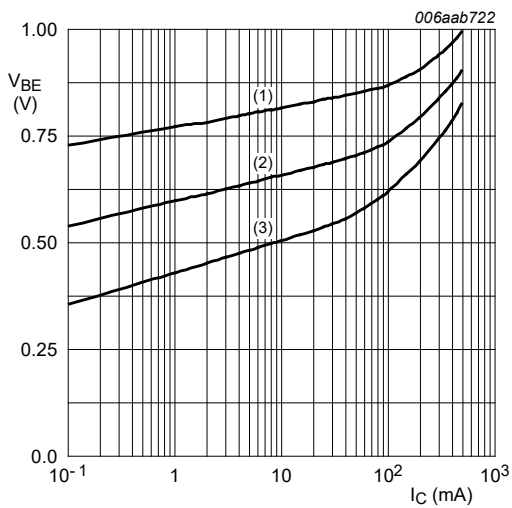
(3)  $T_{amb} = -55 \text{ }^\circ\text{C}$

**Fig. 3. DC current gain as a function of collector current; typical values**



$T_{amb} = 25 \text{ }^\circ\text{C}$

**Fig. 4. Collector current as a function of collector-emitter voltage; typical values**



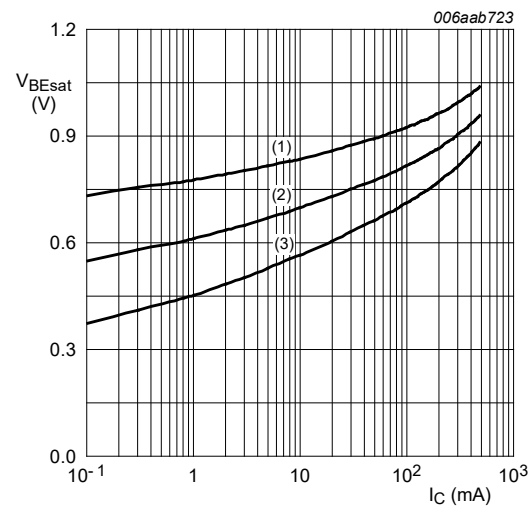
$V_{CE} = 10 \text{ V}$

(1)  $T_{amb} = -55 \text{ }^\circ\text{C}$

(2)  $T_{amb} = 25 \text{ }^\circ\text{C}$

(3)  $T_{amb} = 100 \text{ }^\circ\text{C}$

**Fig. 5. Base-emitter voltage as a function of collector current; typical values**



$I_C/I_B = 5$

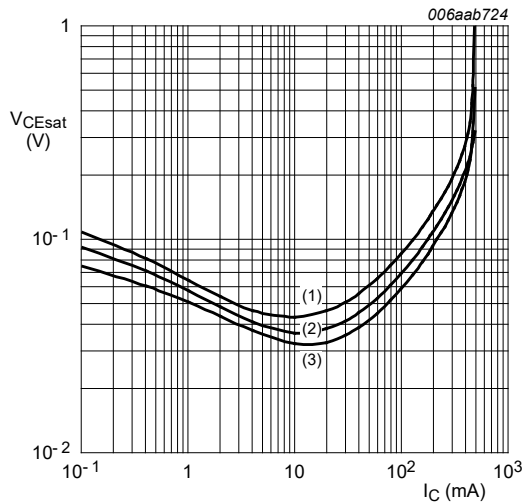
(1)  $T_{amb} = -55 \text{ }^\circ\text{C}$

(2)  $T_{amb} = 25 \text{ }^\circ\text{C}$

(3)  $T_{amb} = 100 \text{ }^\circ\text{C}$

**Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values**

## 500 V, 150 mA NPN high-voltage low VCEsat (BISS) transistor



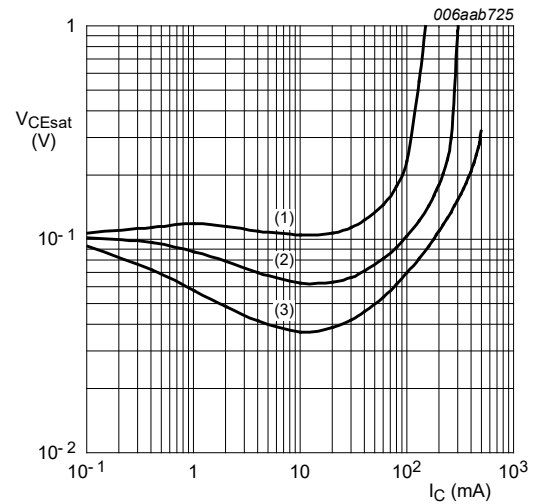
$$I_C/I_B = 5$$

(1)  $T_{amb} = 100\text{ °C}$

(2)  $T_{amb} = 25\text{ °C}$

(3)  $T_{amb} = -55\text{ °C}$

**Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values**



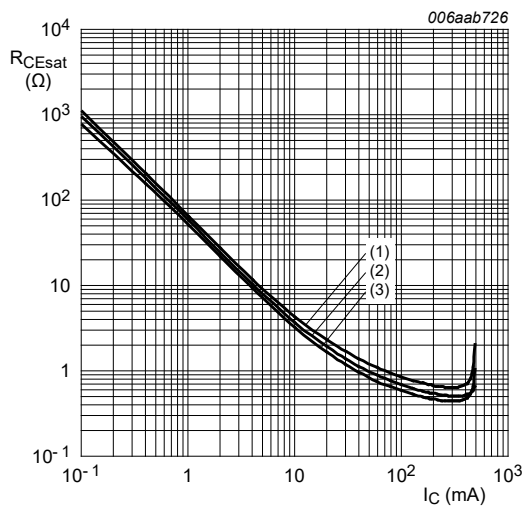
$$T_{amb} = 25\text{ °C}$$

(1)  $I_C/I_B = 20$

(2)  $I_C/I_B = 10$

(3)  $I_C/I_B = 5$

**Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values**



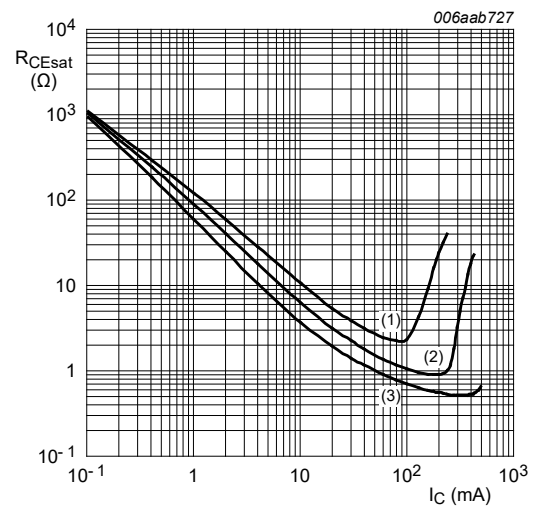
$$I_C/I_B = 5$$

(1)  $T_{amb} = 100\text{ °C}$

(2)  $T_{amb} = 25\text{ °C}$

(3)  $T_{amb} = -55\text{ °C}$

**Fig. 9. Collector-emitter saturation resistance as a function of collector current; typical values**



$$T_{amb} = 25\text{ °C}$$

(1)  $I_C/I_B = 20$

(2)  $I_C/I_B = 10$

(3)  $I_C/I_B = 5$

**Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values**



## 11. Test information

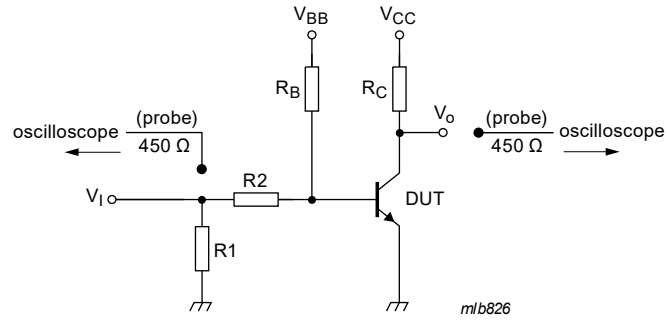


Fig. 11. Test circuit for switching times

### Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 12. Package outline

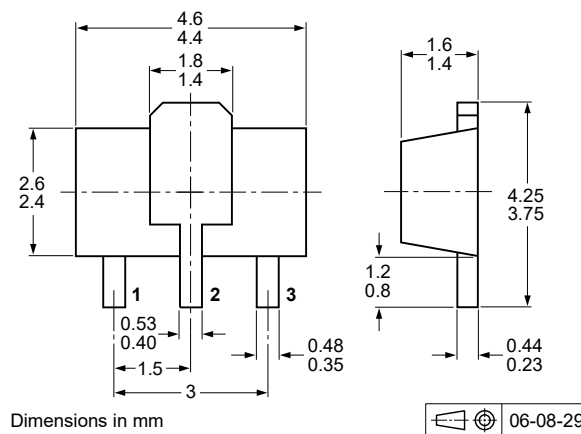


Fig. 12. Package outline SOT89

### 13. Soldering

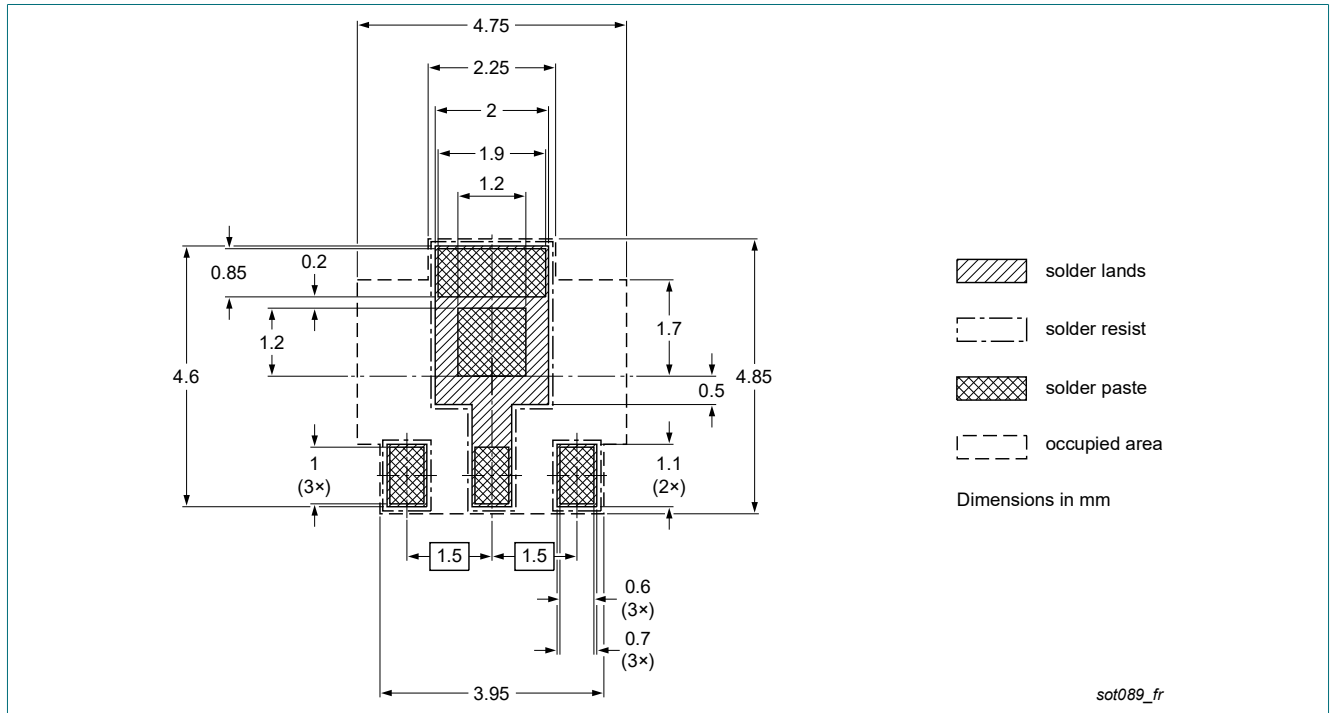


Fig. 13. Reflow soldering footprint for SOT89

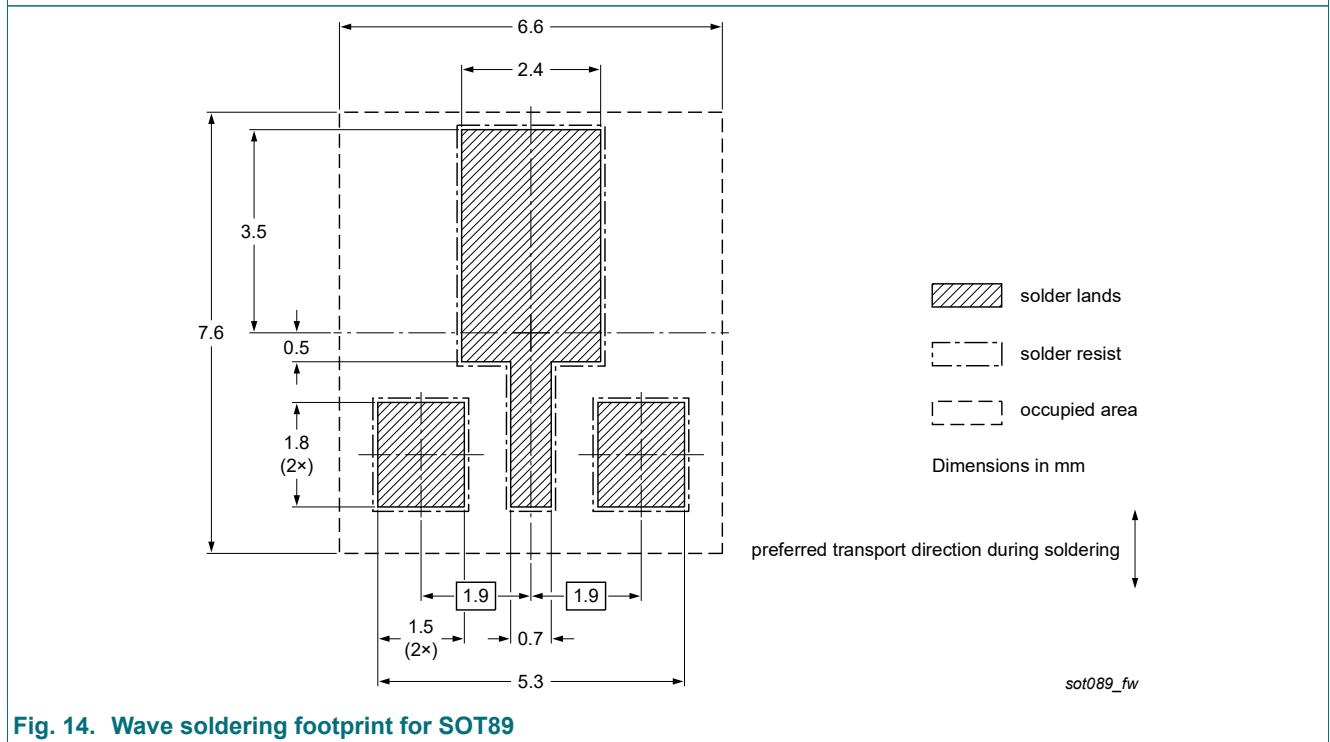


Fig. 14. Wave soldering footprint for SOT89

## 14. Revision history

**Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV8550X v.4	20241009	Product data sheet	-	PBHV8550X v.2
Modifications:	• Figure 1: graph exchanged			
PBHV8550X v.3	20200608	Product data sheet	-	PBHV8550X v.2
PBHV8550X v.2	20200214	Objective data sheet	-	PBHV8550X v.1
PBHV8550X v.1	20200130	Objective data sheet	-	-

## 500 V, 150 mA NPN high-voltage low VCEsat (BISS) transistor

## 15. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 9 October 2024

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